

TOSHIBA LED LAMP InGaAsP RED LIGHT EMISSION

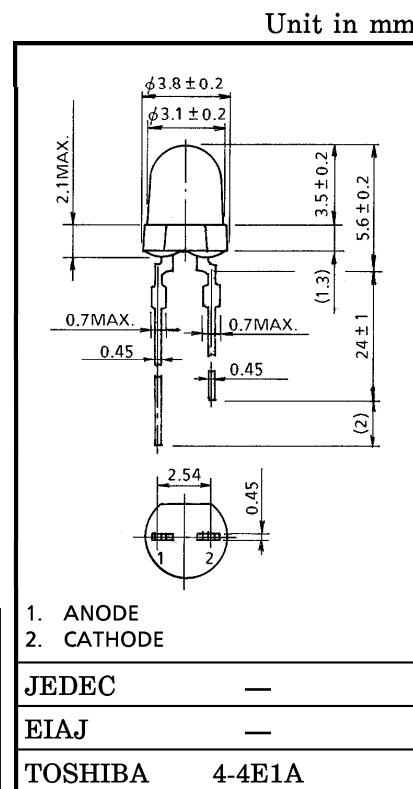
TLSH 125

PANEL CIRCUIT INDICATOR

- 3.1 mm DIAMETER (T1-3 / 4)
- InGaAlP RED LED
- Colorless Transparent Lens
- Low Drive Current, High Intensity RED Light Emission
Recommended Forward Current : $I_F = 1 \sim 20$ mA (DC)
- All Plastic Molded Lens, Provides an Excellent ON-OFF Contrast Ratio.
- Fast Response Time, Capable of Pulse Operation.
- APPLICATIONS : Indicator, Backlight

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current	I_F	50	mA
Reverse Voltage	V_R	4	V
Power Dissipation	P_D	125	mW
Operating Temperature Range	T_{opr}	$-30\sim 85$	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	$-40\sim 120$	$^{\circ}\text{C}$



Weight : 0.14 g

ELECTRICAL AND OPTICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	—	2.1	2.5	V
Reverse Current	I_R	$V_R = 4 \text{ V}$	—	—	50	μA
Luminous Intensity	I_V	$I_F = 20 \text{ mA}$ (Note)	272	800	—	mcd
Peak Emission Wavelength	λ_P	$I_F = 20 \text{ mA}$	—	623	—	nm
Spectral Line Half Width	$\Delta\lambda$	$I_F = 20 \text{ mA}$	—	15	—	nm
Dominant Wavelength	λ_d	$I_F = 20 \text{ mA}$	—	613	—	nm

(Note) : Lamps are classified into the following ranks according to their luminous intensity.

Measurement tolerance for each limit is $\pm 15\%$.

Q : 320~640 mcd, R : 560~1120 mcd, S : 1000~2000 mcd

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PRECAUTION

Please be careful of the followings

- Soldering temperature : 260°C max Soldering time : 3 s max
(Soldering portion of lead : up to 2 mm from the body of the device)
- If the lead is formed, the lead should be formed up to 5 mm from the body of the device without forming stress to the resin. Soldering should be performed after lead forming.
- This visible LED lamp also emits some IR light. If a photodetector is located near the LED lamp, please ensure that it will not be affected by this IR light.

